

**光鋳科技股份有限公司**  
**Epileds Technologies, Inc.**  
 Product specification of 12 x10 mil green chip

1. Scope:

This specification applies to InGaN/GaN 12 x 10mil green chip, EL-G1210A-A1 ◦

2. Materials :

2.1 P-contact : Conductive Layer ◦

2.2 P-pad : Au ◦

2.3 N-pad : Au ◦

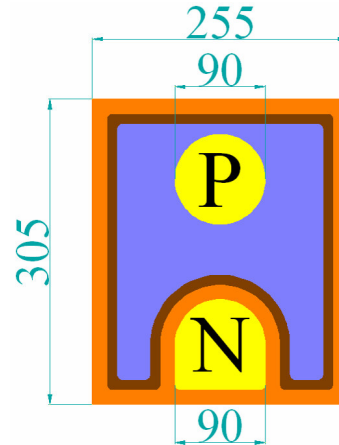
3. Dimensions :

3.1 Chip size : 305±20µm x 255±20µm ◦

3.2 P-pad : φ90±10µm, thickness 1.2±0.1µm ◦

3.3 N-pad : φ90±10µm, thickness 1.2±0.1µm ◦

3.4 Chip thickness : 90µm±10µm ◦



4. Electro-optical characteristics and specification: (Tc=25°C)

4.1 Electro-optical characteristics

Test parameter	Condition	Min	Typ	Max	Unit
Dominant wavelength(Wd)	20mA	500	-	540	nm
Luminous intensity(Iv)	20mA	125	-	640	mcd
Forward voltage(Vf4)	1uA	1.7	-	2.5	V
Forward voltage(Vf1)	20mA	2.8	-	3.8	V
Reverse current (Ir)	-8V	0	-	0.5	uA
Electrostatic discharge characteristic (ESD)	HBM	1000	-	-	V

4.2 Electro-optical specification(Bin table) :

Wd				Iv				Vf1 (V)	Vf4 (V)	Ir (uA)
Bin	nm	Bin	nm	Bin	mcd	Bin	mcd			
GA	500~502.5	GI	520~522.5	13	125~150	D4	370~410	2.8~3.8	1.7~2.5	0~0.5
GB	502.5~505	GJ	522.5~525	14	150~180	D5	410~440			
GC	505~507.5	GK	525~527.5	15	180~220	20	440~530			
GD	507.5~510	GL	527.5~530	16	220~260	21	530~640			
GE	510~512.5	GM	530~532.5	D0	260~285					
GF	512.5~515	GN	532.5~535	D1	285~310					
GG	515~517.5	GO	535~537.5	D2	310~340					
GH	517.5~520	GP	537.5~540	D3	340~370					

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\* The detail technical and reliability datasheet are also available for your reference, please be free to contact us.